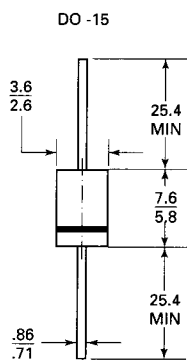


1N5391...1N5399
PLASTIC SILICON RECTIFIERS

FEATURES

- * Low forward voltage
- * High current capability
- * Low leakage current
- * High surge capability
- * Low cost



VOLTAGE RANCE
50 to 1000 Volts
CURRENT
1.5 Amperes

Dimensions in mm

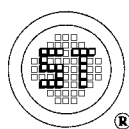
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperture unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

	1N5391	1N5392	1N5393	1N5394	1N5395	1N5396	1N5397	1N5398	1N5399	UNITS
Maximum Recurrent Peak Reverse Voltage*	50	100	200	300	400	500	600	800	1000	V
Maximum RMS Voltage*	35	70	140	210	280	350	420	560	700	V
Maximum DC Blocking Voltage*	50	100	200	300	400	500	600	800	1000	V
Maximum Average Forward Rectified Current .375", 9.5mm Lead Length at T _A = 70 °C	1.5									A
Peak Forward Surge Current 8.3 ms single half sine-wave	60									A
Maximum Forward Voltage at 1.5A Peak	1.4									V
Maximum Reverse Current, Rated DC Blocking Voltage	5.0									μA
Maximum Full Load Reverse Current, Full Cycle Average, .375", 9.5 mm Lead Length at T _A = 55 °C	30									μA
Typical Junction Capacitance (Note 1)	25									pF
Typical Reverse Recovery Time (Note 2)	2									μs
Operating and Storage Temperature Range T _A	-65 to + 175									°C

NOTES:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0 V_{DC}
2. Measured with I_F = 0.5A, I_R = 1A, I_{rr} = .25A



SEMTECH ELECTRONICS LTD.
(wholly owned subsidiary of HONEY TECHNOLOGY LTD.)



1N5391...1N5399

PLASTIC SILICON RECTIFIERS

Fig. 1 — TYPICAL FORWARD CHARACTERISTICS

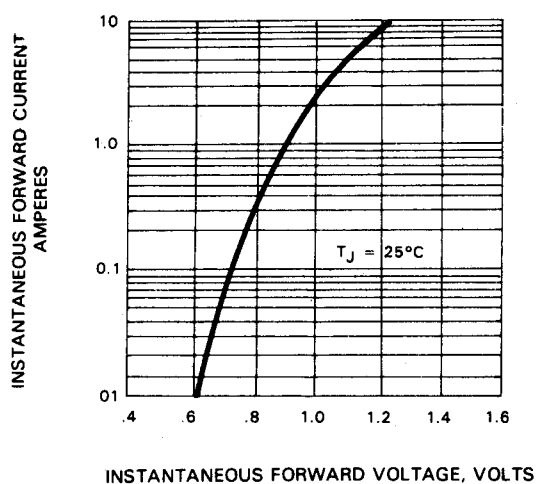


Fig. 2 — PEAK FORWARD SURGE CURRENT

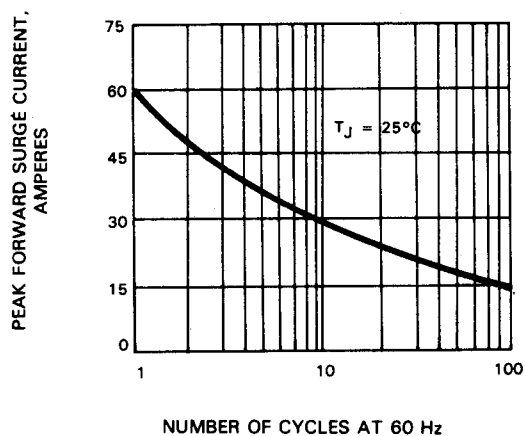


Fig. 3 — FORWARD CURRENT DERATING CURVE

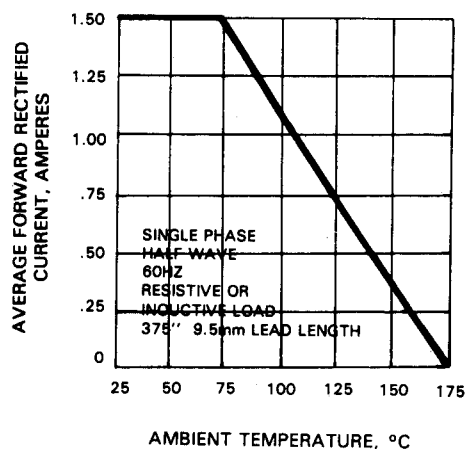
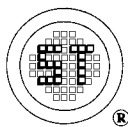
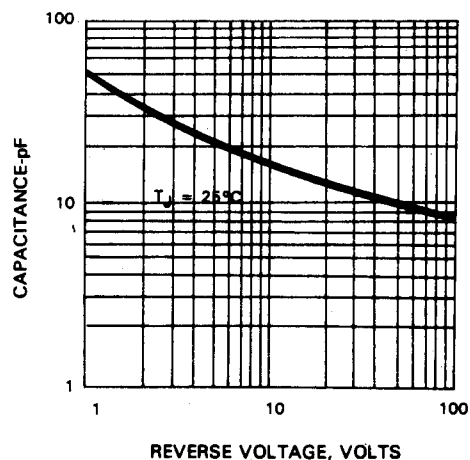


Fig. 4 — TYPICAL JUNCTION CAPACITANCE



SEMTECH ELECTRONICS LTD.

(wholly owned subsidiary of HONEY TECHNOLOGY LTD.)

